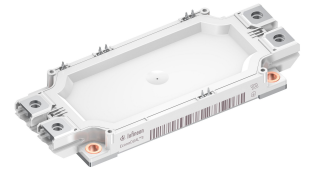


Final datasheet

EconoDUAL™3 module with TRENCHSTOP™IGBT7 and emitter controlled 7 diode and PressFIT / NTC

Features

- Electrical features
 - $V_{CES} = 1700\text{ V}$
 - $I_{C\text{ nom}} = 750\text{ A} / I_{CRM} = 1500\text{ A}$
 - Integrated temperature sensor
 - High current density
 - Low $V_{CE,sat}$
 - Overload operation up to 175°C
 - TRENCHSTOP™ IGBT7
 - $V_{CE,sat}$ with positive temperature coefficient
 - Enlarged diode for regenerative operation
- Mechanical features
 - High power density
 - Isolated base plate
 - PressFIT contact technology
 - Standard housing



Potential applications

- High-power converters
- Medium-voltage converters
- Motor drives
- Wind turbines
- Power transmission and distribution

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description

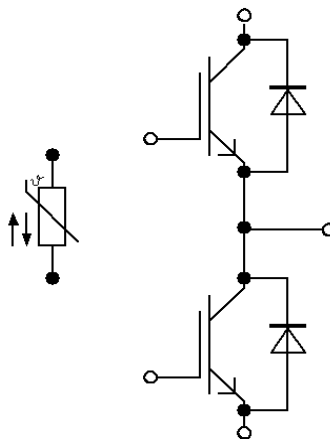


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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, $f = 50$ Hz, $t = 1$ min	3.4	kV
Isolation test voltage NTC	$V_{ISOL(NTC)}$	RMS, $f = 50$ Hz	3.4	kV
Material of module baseplate			Cu	
Internal isolation		basic insulation (class 1, IEC 61140)	Al2O3	
Creepage distance	$d_{Creep\ nom}$	terminal to baseplate, nom., (PD2, IEC 60664-1, Ed. 3.0)	> 15	mm
Creepage distance	$d_{Creep\ min}$	terminal to baseplate, min., (PD2, IEC 60664-1, Ed. 3.0)	14.7	mm
Creepage distance	$d_{Creep\ nom}$	terminal to terminal, nom., (PD2, IEC 60664-1, Ed. 3.0)	12.1	mm
Creepage distance	$d_{Creep\ min}$	terminal to terminal, min., (PD2, IEC 60664-1, Ed. 3.0)	11.5	mm
Clearance	$d_{Clear\ nom}$	terminal to baseplate, nom.	> 12.5	mm
Clearance	$d_{Clear\ min}$	terminal to baseplate, min.	12.5	mm
Clearance	$d_{Clear\ nom}$	terminal to terminal, nom.	10.0	mm
Clearance	$d_{Clear\ min}$	terminal to terminal, min.	9.6	mm
Comparative tracking index	CTI		> 200	
Relative thermal index (electrical)	RTI	housing	140	°C

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	L_{sCE}			20		nH
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_C = 25$ °C, per switch		0.8		mΩ
Storage temperature	T_{stg}		-40		125	°C
Mounting torque for module mounting	M	- Mounting according to valid application note	M5, Screw	3	6	Nm
Terminal connection torque	M	- Mounting according to valid application note	M6, Screw	3	6	Nm
Weight	G			345		g

2 IGBT, Inverter

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Collector-emitter voltage	V_{CES}	$T_{vj} = 25\text{ °C}$		1700		V
Continuous DC collector current	I_{CDC}	$T_{vj\text{ max}} = 175\text{ °C}$ $T_C = 80\text{ °C}$		750		A
Maximum RMS module DC-terminal current	I_{tRMS}	$T_{\text{Terminal}} = 90\text{ °C}$, $T_C = 90\text{ °C}$		580		A
			$T_{\text{Terminal}} = 105\text{ °C}$, $T_C = 90\text{ °C}$		565	
Repetitive peak collector current	I_{CRM}	t_p limited by $T_{vj\text{ op}}$		1500		A
Gate-emitter peak voltage	V_{GES}			±20		V

Table 4 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Collector-emitter saturation voltage	$V_{CE\text{ sat}}$	$I_C = 750\text{ A}$, $V_{GE} = 15\text{ V}$	$T_{vj} = 25\text{ °C}$		1.70	1.85	V
			$T_{vj} = 125\text{ °C}$		1.95		
			$T_{vj} = 150\text{ °C}$		2.05		
			$T_{vj} = 175\text{ °C}$		2.10		
Gate threshold voltage	V_{GEth}	$I_C = 15.7\text{ mA}$, $V_{CE} = V_{GE}$, $T_{vj} = 25\text{ °C}$	5.15	5.80	6.45	V	
Gate charge	Q_G	$V_{GE} = \pm 15\text{ V}$, $V_{CC} = 900\text{ V}$		7.15		μC	
Internal gate resistor	R_{Gint}	$T_{vj} = 25\text{ °C}$		0.33		Ω	
Input capacitance	C_{ies}	$f = 100\text{ kHz}$, $T_{vj} = 25\text{ °C}$, $V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$		78.1		nF	
Reverse transfer capacitance	C_{res}	$f = 100\text{ kHz}$, $T_{vj} = 25\text{ °C}$, $V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$		0.275		nF	
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 1700\text{ V}$, $V_{GE} = 0\text{ V}$ $T_{vj} = 25\text{ °C}$			5	mA	
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\text{ V}$, $V_{GE} = 20\text{ V}$, $T_{vj} = 25\text{ °C}$			100	nA	
Turn-on delay time (inductive load)	t_{don}	$I_C = 750\text{ A}$, $V_{CC} = 900\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 0.51\text{ Ω}$	$T_{vj} = 25\text{ °C}$		0.158		μs
			$T_{vj} = 125\text{ °C}$		0.172		
			$T_{vj} = 150\text{ °C}$		0.178		
			$T_{vj} = 175\text{ °C}$		0.184		

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rise time (inductive load)	t_r	$I_C = 750 \text{ A}, V_{CC} = 900 \text{ V}, V_{GE} = \pm 15 \text{ V}, R_{Gon} = 0.51 \Omega$	$T_{vj} = 25 \text{ }^\circ\text{C}$	0.046		μs
			$T_{vj} = 125 \text{ }^\circ\text{C}$	0.053		
			$T_{vj} = 150 \text{ }^\circ\text{C}$	0.055		
			$T_{vj} = 175 \text{ }^\circ\text{C}$	0.057		
Turn-off delay time (inductive load)	t_{doff}	$I_C = 750 \text{ A}, V_{CC} = 900 \text{ V}, V_{GE} = \pm 15 \text{ V}, R_{Goff} = 2.2 \Omega$	$T_{vj} = 25 \text{ }^\circ\text{C}$	0.536		μs
			$T_{vj} = 125 \text{ }^\circ\text{C}$	0.613		
			$T_{vj} = 150 \text{ }^\circ\text{C}$	0.631		
			$T_{vj} = 175 \text{ }^\circ\text{C}$	0.648		
Fall time (inductive load)	t_f	$I_C = 750 \text{ A}, V_{CC} = 900 \text{ V}, V_{GE} = \pm 15 \text{ V}, R_{Goff} = 2.2 \Omega$	$T_{vj} = 25 \text{ }^\circ\text{C}$	0.231		μs
			$T_{vj} = 125 \text{ }^\circ\text{C}$	0.450		
			$T_{vj} = 150 \text{ }^\circ\text{C}$	0.525		
			$T_{vj} = 175 \text{ }^\circ\text{C}$	0.599		
Turn-on energy loss per pulse	E_{on}	$I_C = 750 \text{ A}, V_{CC} = 900 \text{ V}, L_\sigma = 25 \text{ nH}, V_{GE} = \pm 15 \text{ V}, R_{Gon} = 0.51 \Omega, di/dt = 11.1 \text{ kA}/\mu\text{s} (T_{vj} = 175 \text{ }^\circ\text{C})$	$T_{vj} = 25 \text{ }^\circ\text{C}$	74		mJ
			$T_{vj} = 125 \text{ }^\circ\text{C}$	171		
			$T_{vj} = 150 \text{ }^\circ\text{C}$	204		
			$T_{vj} = 175 \text{ }^\circ\text{C}$	238		
Turn-off energy loss per pulse	E_{off}	$I_C = 750 \text{ A}, V_{CC} = 900 \text{ V}, L_\sigma = 25 \text{ nH}, V_{GE} = \pm 15 \text{ V}, R_{Goff} = 2.2 \Omega, dv/dt = 3600 \text{ V}/\mu\text{s} (T_{vj} = 175 \text{ }^\circ\text{C})$	$T_{vj} = 25 \text{ }^\circ\text{C}$	132		mJ
			$T_{vj} = 125 \text{ }^\circ\text{C}$	208		
			$T_{vj} = 150 \text{ }^\circ\text{C}$	224		
			$T_{vj} = 175 \text{ }^\circ\text{C}$	239		
SC data	I_{SC}	$V_{GE} = 15 \text{ V}, V_{CC} = 1000 \text{ V}, V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$	$t_p \leq 8 \mu\text{s}, T_{vj} = 150 \text{ }^\circ\text{C}$	2600		A
			$t_p \leq 6 \mu\text{s}, T_{vj} = 175 \text{ }^\circ\text{C}$	2500		
Thermal resistance, junction to case	R_{thJC}	per IGBT			0.0551	K/W
Thermal resistance, case to heat sink	R_{thCH}	per IGBT, $\lambda_{grease} = 1 \text{ W}/(\text{m}\cdot\text{K})$		0.0345		K/W
Temperature under switching conditions	T_{vjop}		-40		175	$^\circ\text{C}$

Note: $T_{vjop} > 150 \text{ }^\circ\text{C}$ is only allowed for operation at overload conditions. For detailed specifications please refer to AN 2018-14.

3 Diode, Inverter

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Repetitive peak reverse voltage	V_{RRM}		$T_{vj} = 25\text{ °C}$		1700		V
Implemented forward current	I_{FN}				1200		A
Continuous DC forward current	I_F				750		A
Repetitive peak forward current	I_{FRM}	$t_p = 1\text{ ms}$			1500		A
I^2t - value	I^2t	$t_p = 10\text{ ms}, V_R = 0\text{ V}$	$T_{vj} = 125\text{ °C}$		48300		A^2s
			$T_{vj} = 175\text{ °C}$		37200		

Table 6 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 750\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$		2.00	2.15	V
			$T_{vj} = 125\text{ °C}$		1.85		
			$T_{vj} = 150\text{ °C}$		1.80		
			$T_{vj} = 175\text{ °C}$		1.75		
Peak reverse recovery current	I_{RM}	$V_{CC} = 900\text{ V}, I_F = 750\text{ A}, V_{GE} = -15\text{ V}, -di_F/dt = 11.8\text{ kA}/\mu\text{s} (T_{vj} = 175\text{ °C})$	$T_{vj} = 25\text{ °C}$		950		A
			$T_{vj} = 125\text{ °C}$		1020		
			$T_{vj} = 150\text{ °C}$		1020		
			$T_{vj} = 175\text{ °C}$		1020		
Recovered charge	Q_r	$V_{CC} = 900\text{ V}, I_F = 750\text{ A}, V_{GE} = -15\text{ V}, -di_F/dt = 11.8\text{ kA}/\mu\text{s} (T_{vj} = 175\text{ °C})$	$T_{vj} = 25\text{ °C}$		115		μC
			$T_{vj} = 125\text{ °C}$		218		
			$T_{vj} = 150\text{ °C}$		255		
			$T_{vj} = 175\text{ °C}$		292		
Reverse recovery energy	E_{rec}	$V_{CC} = 900\text{ V}, I_F = 750\text{ A}, V_{GE} = -15\text{ V}, -di_F/dt = 11.8\text{ kA}/\mu\text{s} (T_{vj} = 175\text{ °C})$	$T_{vj} = 25\text{ °C}$		76		mJ
			$T_{vj} = 125\text{ °C}$		132		
			$T_{vj} = 150\text{ °C}$		152		
			$T_{vj} = 175\text{ °C}$		171		
Thermal resistance, junction to case	R_{thJC}	per diode				0.0753	K/W
Thermal resistance, case to heat sink	R_{thCH}	per diode, $\lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$			0.0363		K/W
Temperature under switching conditions	$T_{vj\text{ op}}$			-40		175	$^{\circ}\text{C}$

Note: $T_{vj\ op} > 150^{\circ}\text{C}$ is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

4 NTC-Thermistor

Table 7 Characteristic values

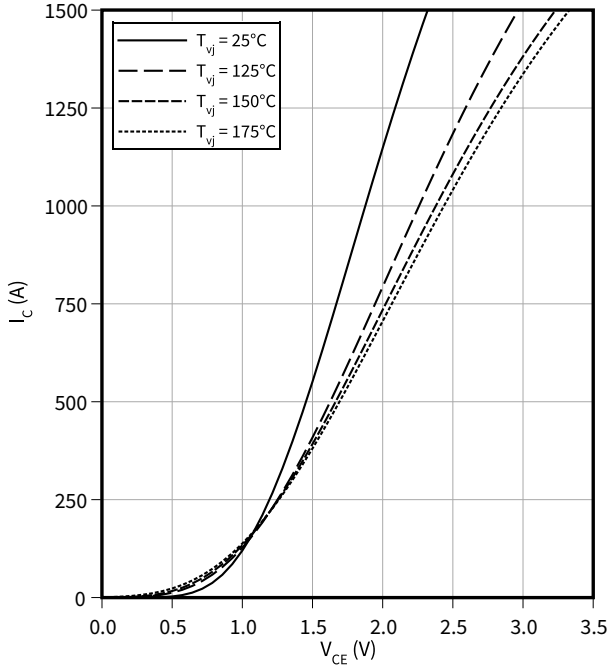
Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	$T_{NTC} = 25^{\circ}\text{C}$		5		k Ω
Deviation of R_{100}	$\Delta R/R$	$T_{NTC} = 100^{\circ}\text{C}$, $R_{100} = 493\ \Omega$	-5		5	%
Power dissipation	P_{25}	$T_{NTC} = 25^{\circ}\text{C}$			20	mW
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2 - 1/(298,15\ \text{K}))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2 - 1/(298,15\ \text{K}))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2 - 1/(298,15\ \text{K}))]$		3433		K

Note: For an analytical description of the NTC characteristics please refer to AN2009-10, chapter 4

5 Characteristics diagrams

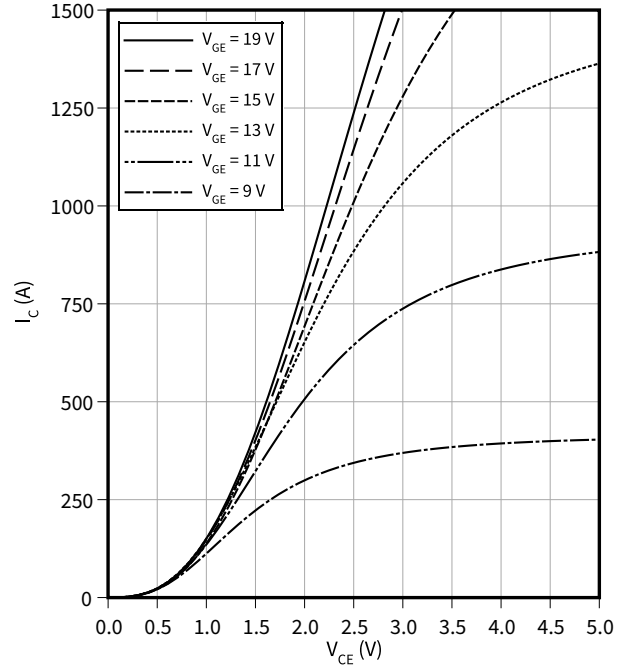
Output characteristic (typical), IGBT, Inverter

$I_C = f(V_{CE})$
 $V_{GE} = 15 \text{ V}$



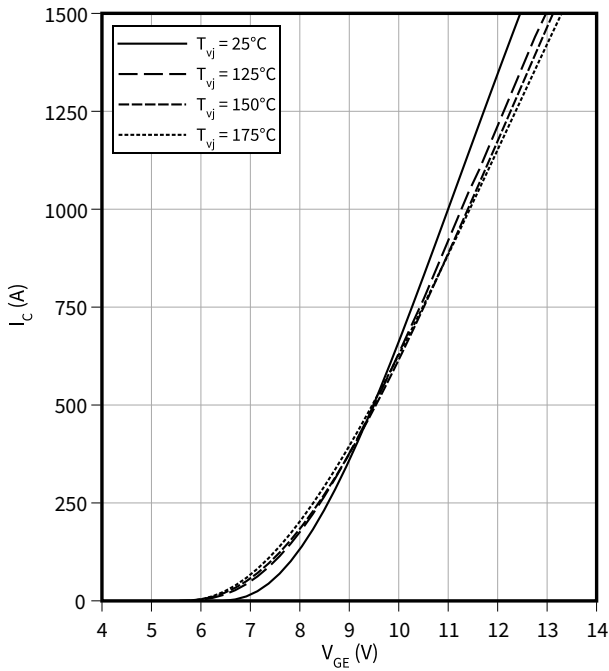
Output characteristic field (typical), IGBT, Inverter

$I_C = f(V_{CE})$
 $T_{vj} = 175 \text{ °C}$



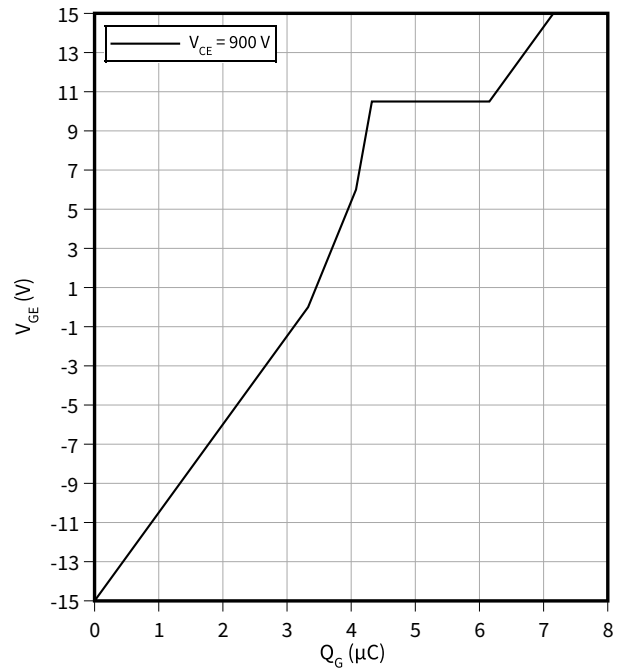
Transfer characteristic (typical), IGBT, Inverter

$I_C = f(V_{GE})$
 $V_{CE} = 20 \text{ V}$



Gate charge characteristic (typical), IGBT, Inverter

$V_{GE} = f(Q_G)$
 $I_C = 750 \text{ A}, T_{vj} = 25 \text{ °C}$

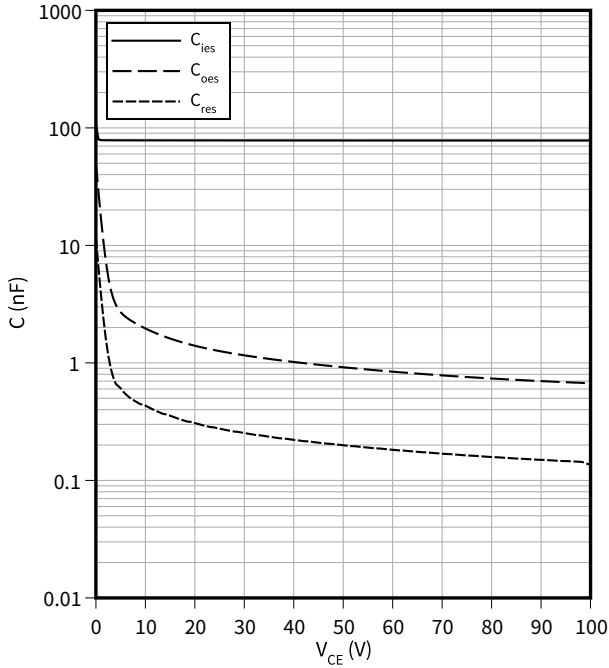


5 Characteristics diagrams

Capacity characteristic (typical), IGBT, Inverter

$C = f(V_{CE})$

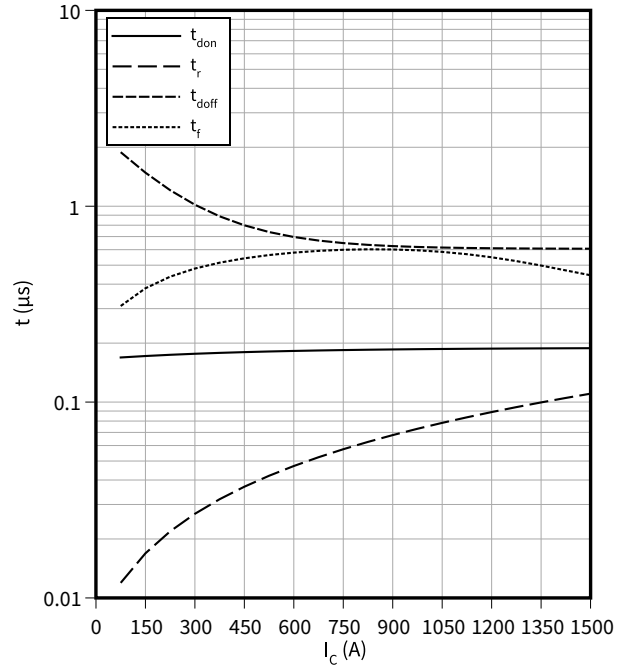
$f = 100 \text{ kHz}, V_{GE} = 0 \text{ V}, T_{vj} = 25 \text{ }^\circ\text{C}$



Switching times (typical), IGBT, Inverter

$t = f(I_C)$

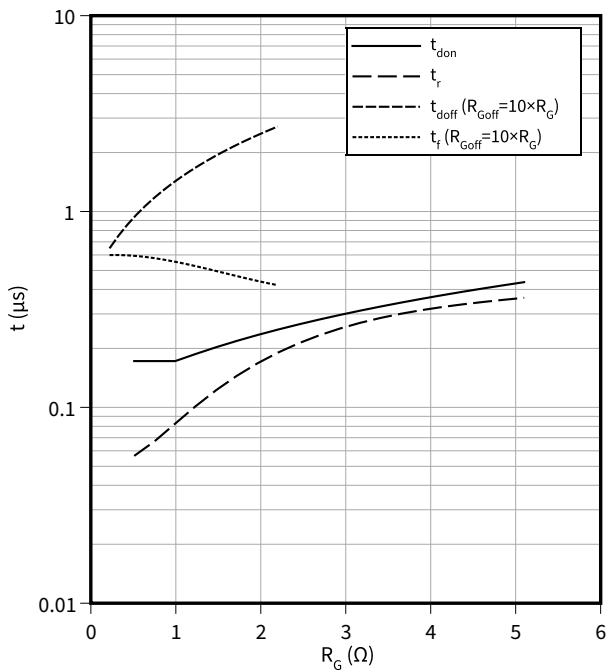
$R_{Goff} = 2.2 \text{ } \Omega, R_{Gon} = 0.51 \text{ } \Omega, V_{CC} = 900 \text{ V}, V_{GE} = \pm 15 \text{ V}, T_{vj} = 175 \text{ }^\circ\text{C}$



Switching times (typical), IGBT, Inverter

$t = f(R_G)$

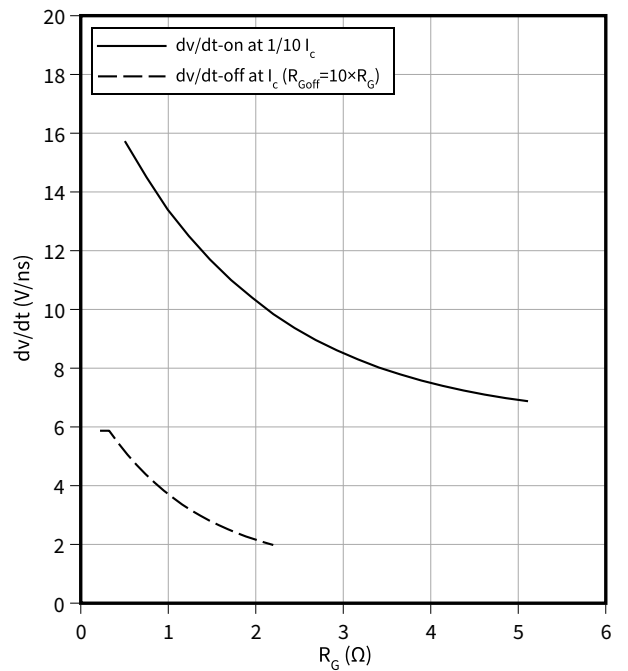
$I_C = 750 \text{ A}, V_{CC} = 900 \text{ V}, V_{GE} = \pm 15 \text{ V}, T_{vj} = 175 \text{ }^\circ\text{C}$



Voltage slope (typical), IGBT, Inverter

$dv/dt = f(R_G)$

$V_{CE} = 900 \text{ V}, V_{GE} = \pm 15 \text{ V}, I_C = 750 \text{ A}, T_{vj} = 25 \text{ }^\circ\text{C}$

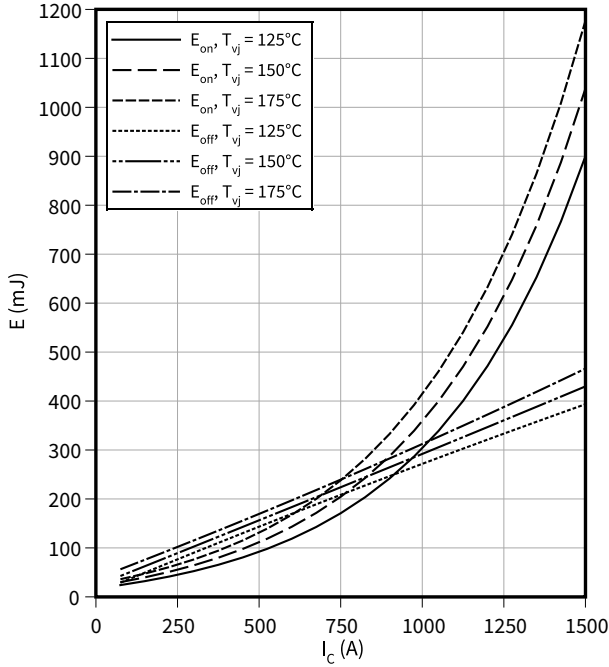


5 Characteristics diagrams

Switching losses (typical), IGBT, Inverter

$E = f(I_C)$

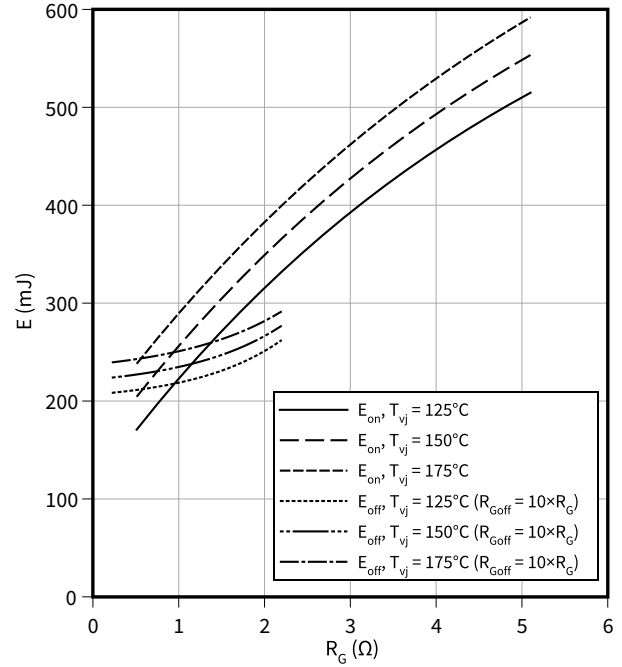
$R_{Goff} = 2.2 \Omega$, $R_{Gon} = 0.51 \Omega$, $V_{CC} = 900 \text{ V}$, $V_{GE} = \pm 15 \text{ V}$



Switching losses (typical), IGBT, Inverter

$E = f(R_G)$

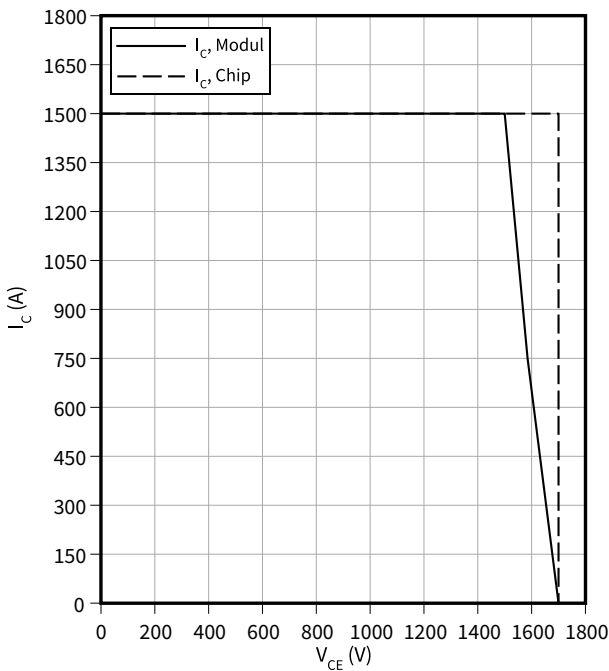
$I_C = 750 \text{ A}$, $V_{CC} = 900 \text{ V}$, $V_{GE} = \pm 15 \text{ V}$



Reverse bias safe operating area (RBSOA), IGBT, Inverter

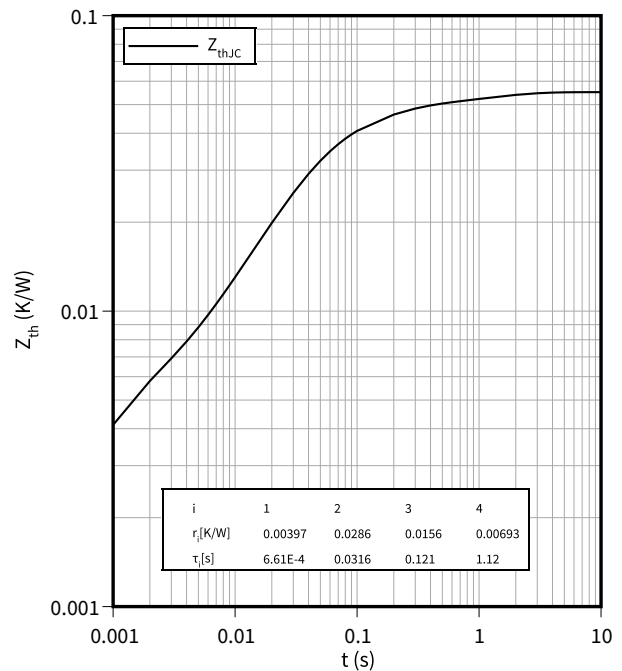
$I_C = f(V_{CE})$

$R_{Goff} = 2.2 \Omega$, $V_{GE} = \pm 15 \text{ V}$, $T_{vj} = 175 \text{ °C}$



Transient thermal impedance, IGBT, Inverter

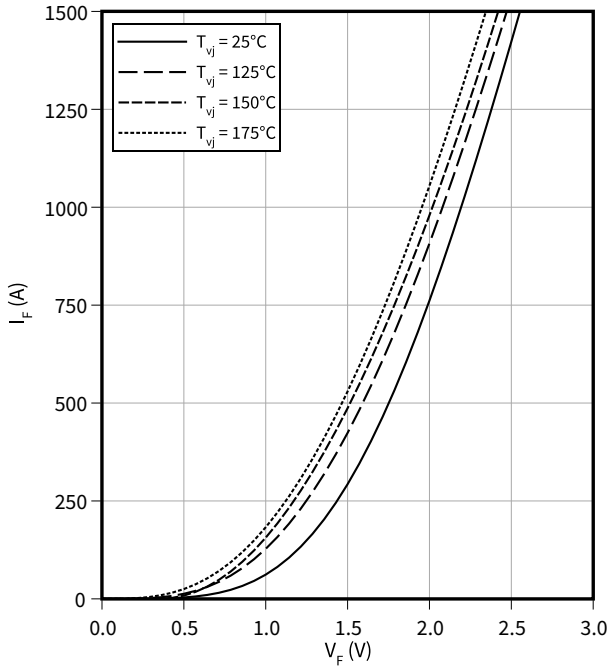
$Z_{th} = f(t)$



5 Characteristics diagrams

Forward characteristic (typical), Diode, Inverter

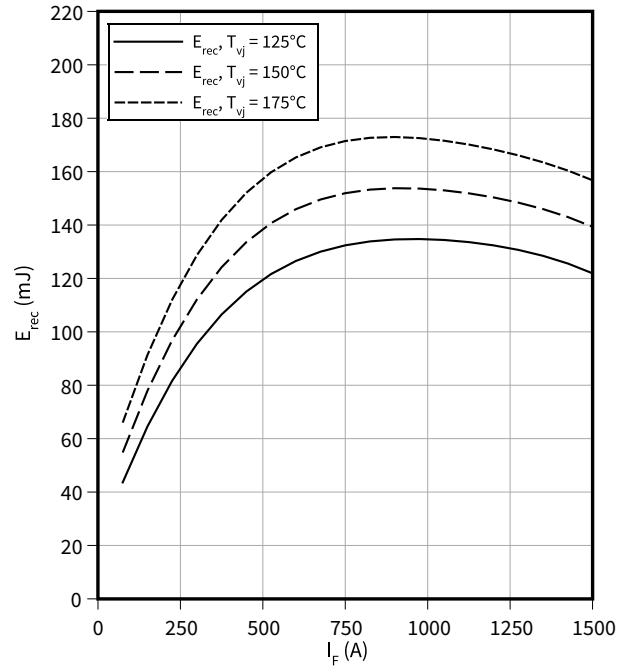
$I_F = f(V_F)$



Switching losses (typical), Diode, Inverter

$E_{rec} = f(I_F)$

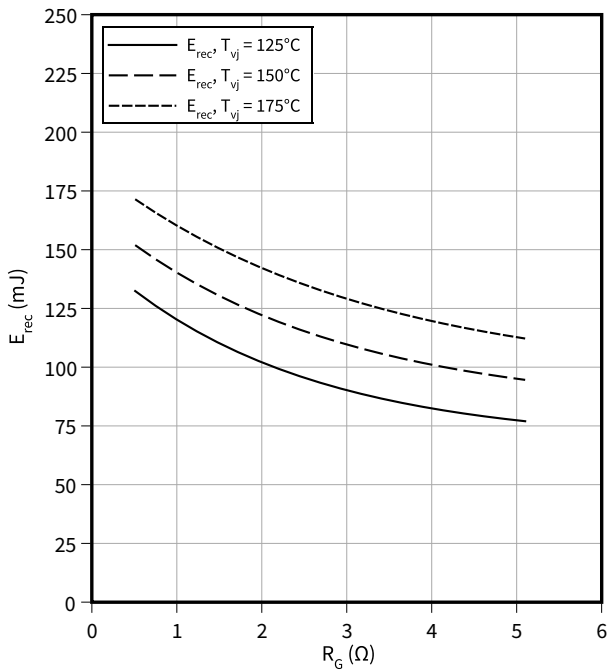
$R_{Gon} = 0.51 \Omega, V_{CC} = 900 \text{ V}$



Switching losses (typical), Diode, Inverter

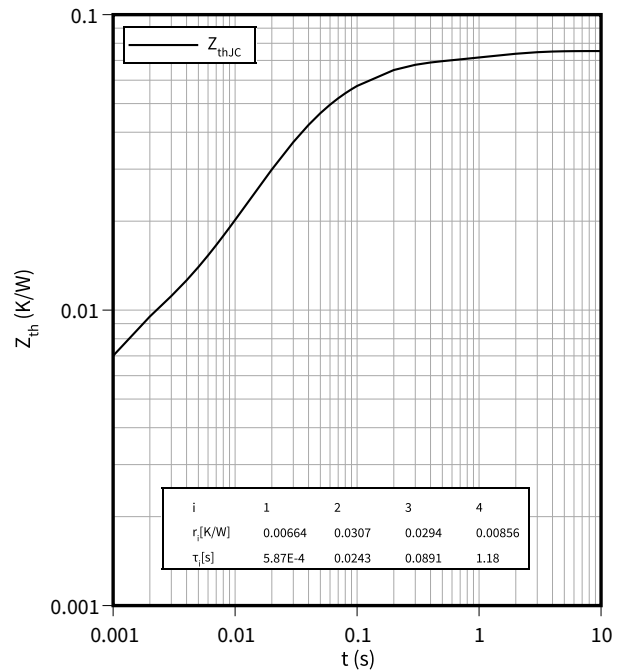
$E_{rec} = f(R_G)$

$I_F = 750 \text{ A}, V_{CC} = 900 \text{ V}$



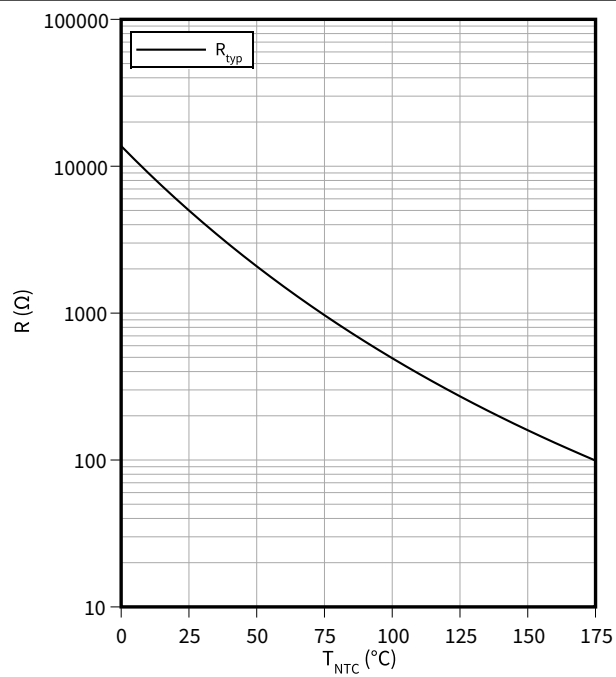
Transient thermal impedance, Diode, Inverter

$Z_{th} = f(t)$



Temperature characteristic (typical), NTC-Thermistor

$$R = f(T_{NTC})$$



6 Circuit diagram

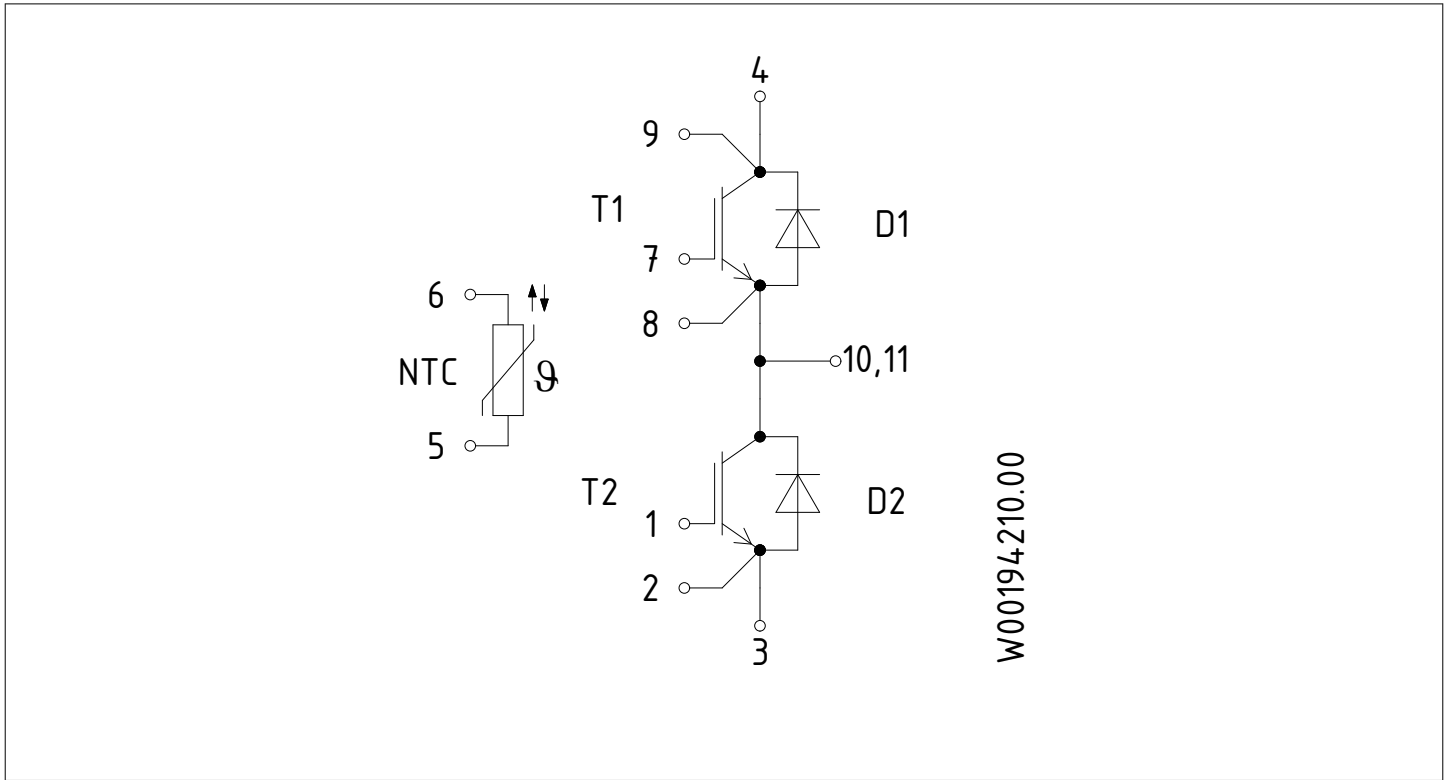


Figure 1

7 Package outlines

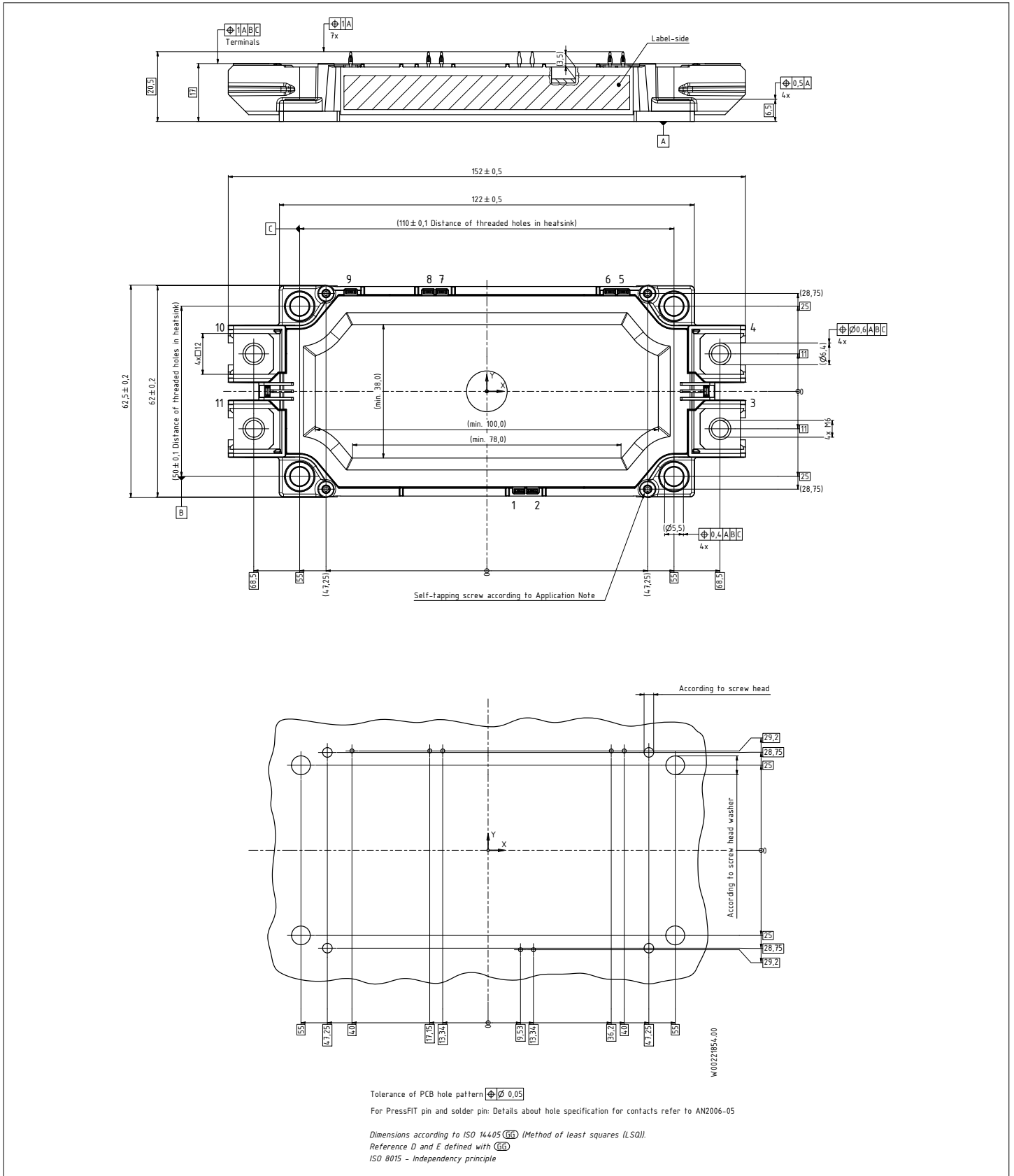


Figure 2

8 Module label code


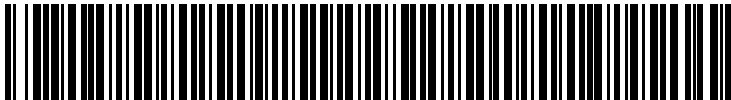
Module label code			
Code format	Data Matrix	Barcode Code128	
Encoding	ASCII text	Code Set A	
Symbol size	16x16	23 digits	
Standard	IEC24720 and IEC16022	IEC8859-1	
Code content	Content	Digit	Example
	Module serial number	1 - 5	71549
	Module material number	6 - 11	142846
	Production order number	12 - 19	55054991
	Date code (production year)	20 - 21	15
	Date code (production week)	22 - 23	30
Example	 		
	71549142846550549911530		71549142846550549911530

Figure 3

Revision history

Document revision	Date of release	Description of changes
0.10	2021-10-20	Initial version
1.00	2022-05-06	Final datasheet
1.10	2024-03-08	Final datasheet

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Except as otherwise explicitly approved by Infineon Technologies in a written document signed by authorized representatives of Infineon Technologies, Infineon Technologies' products may not be used in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury.